

# AGIPD & PERCIVAL

## 2 Mega-Pixel Imagers for FELs

Heinz Graafsma, DESY-Hamburg

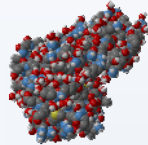


(Adaptive Gain Integrating Pixel Detector)  
a multi-Mega-pixel & multi-Mega-Hz  
X-Ray imager the European XFEL

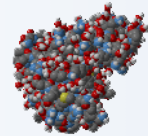
# XFEL requirements (2006)



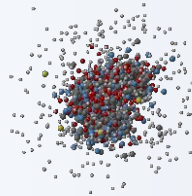
Just before  
XFEL pulse



During the  
pulse



After pulse



Single  
photons

$10^4$  photons  
@ 12keV

352 images

1k x 1k pixels  
(or more)

4.5 MHz

- Time structure of the photon signals

- Pipelined architecture
- Random access mode
- External veto capability

- High radiation dose at small angles:  $10^4$  photons/(pixel shot)

- over 3 years: 1 GGy @sensor

- Radiation damage of silicon sensor
- Radiation damage of underlying electronics ( $\gg 10$  MGy)
- Radiation hard design

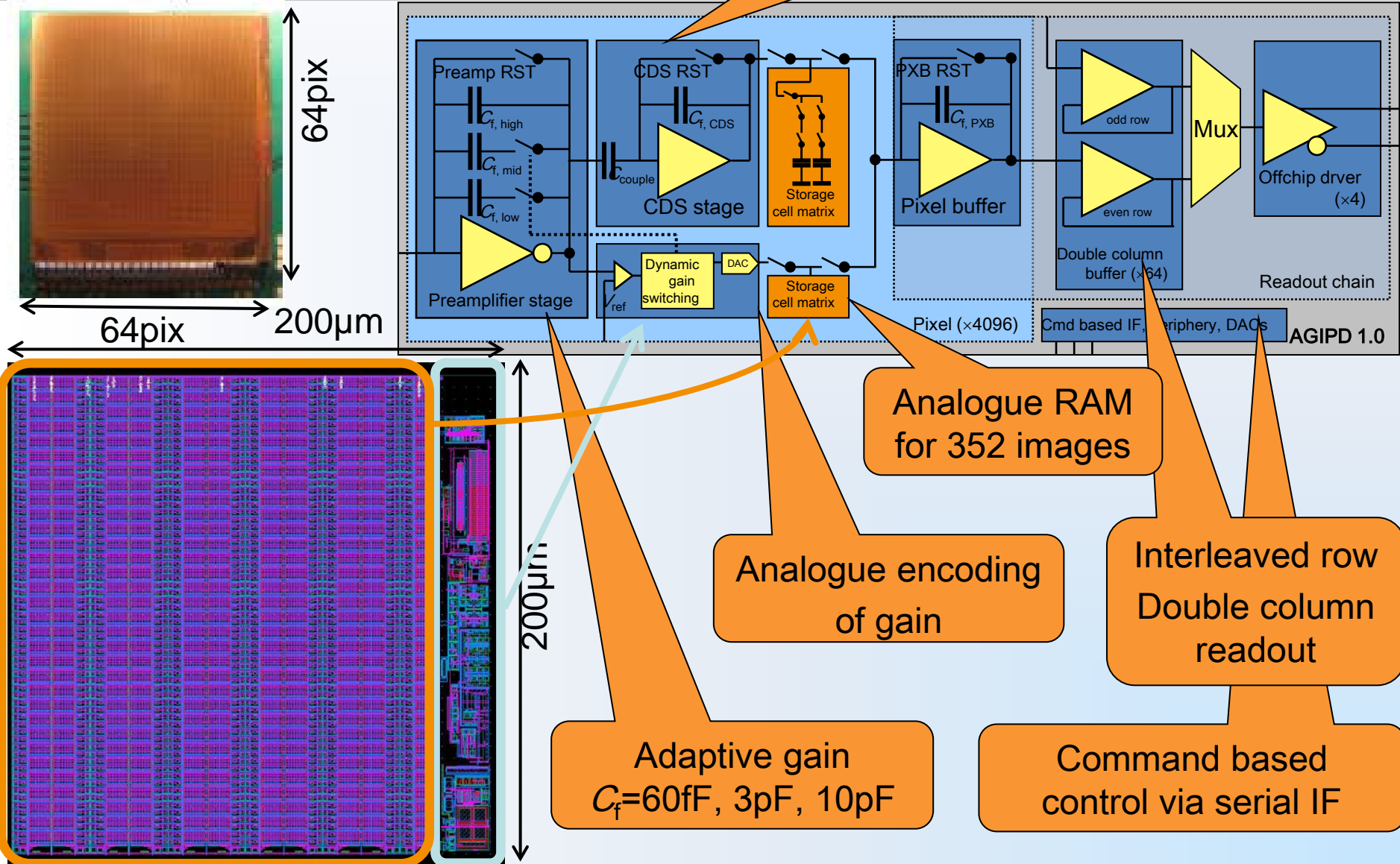
- 500  $\mu\text{m}$  silicon sensor

- 200  $\mu\text{m}$  square pixels

- Vacuum compatibility

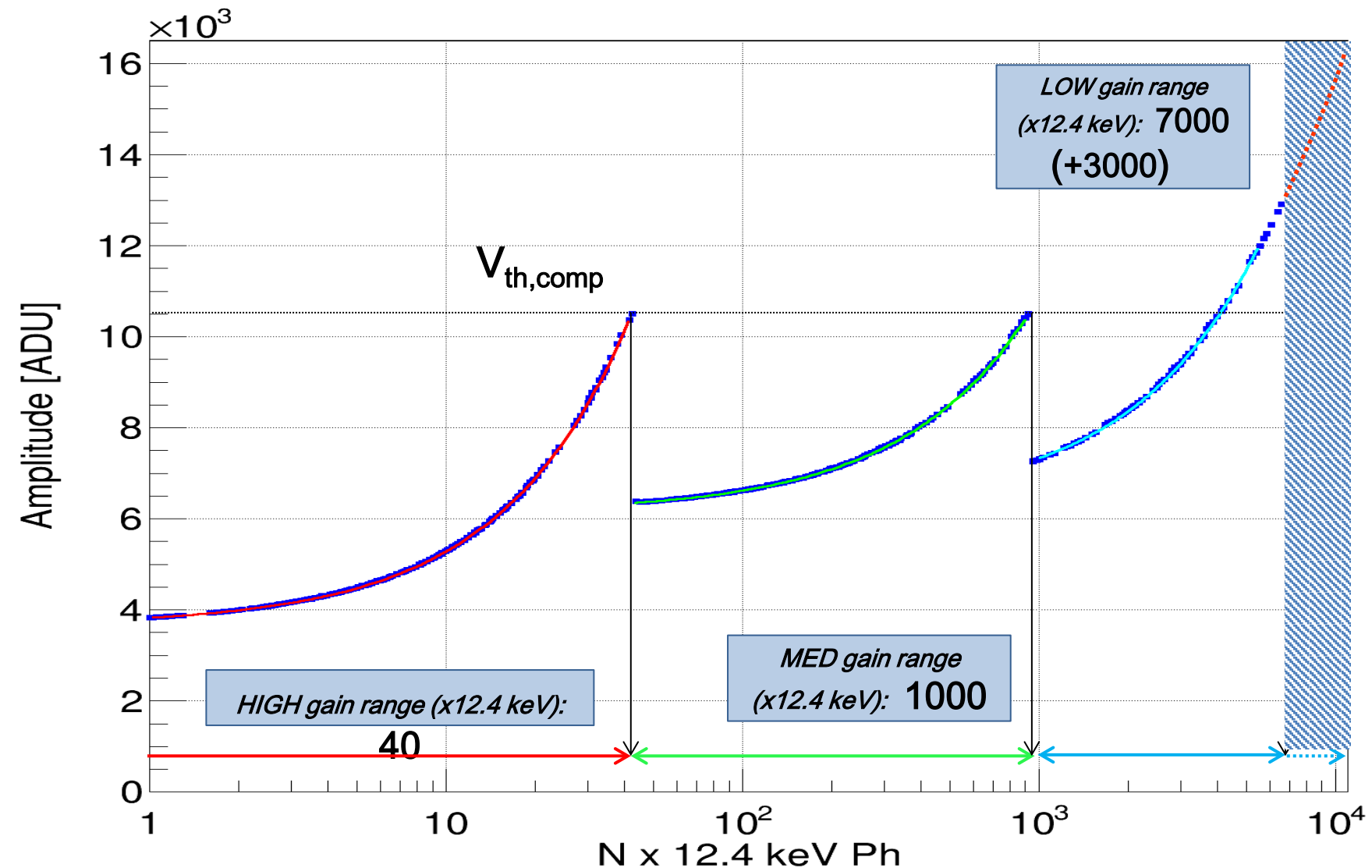
- Detector with central hole

# AGIPD ASIC



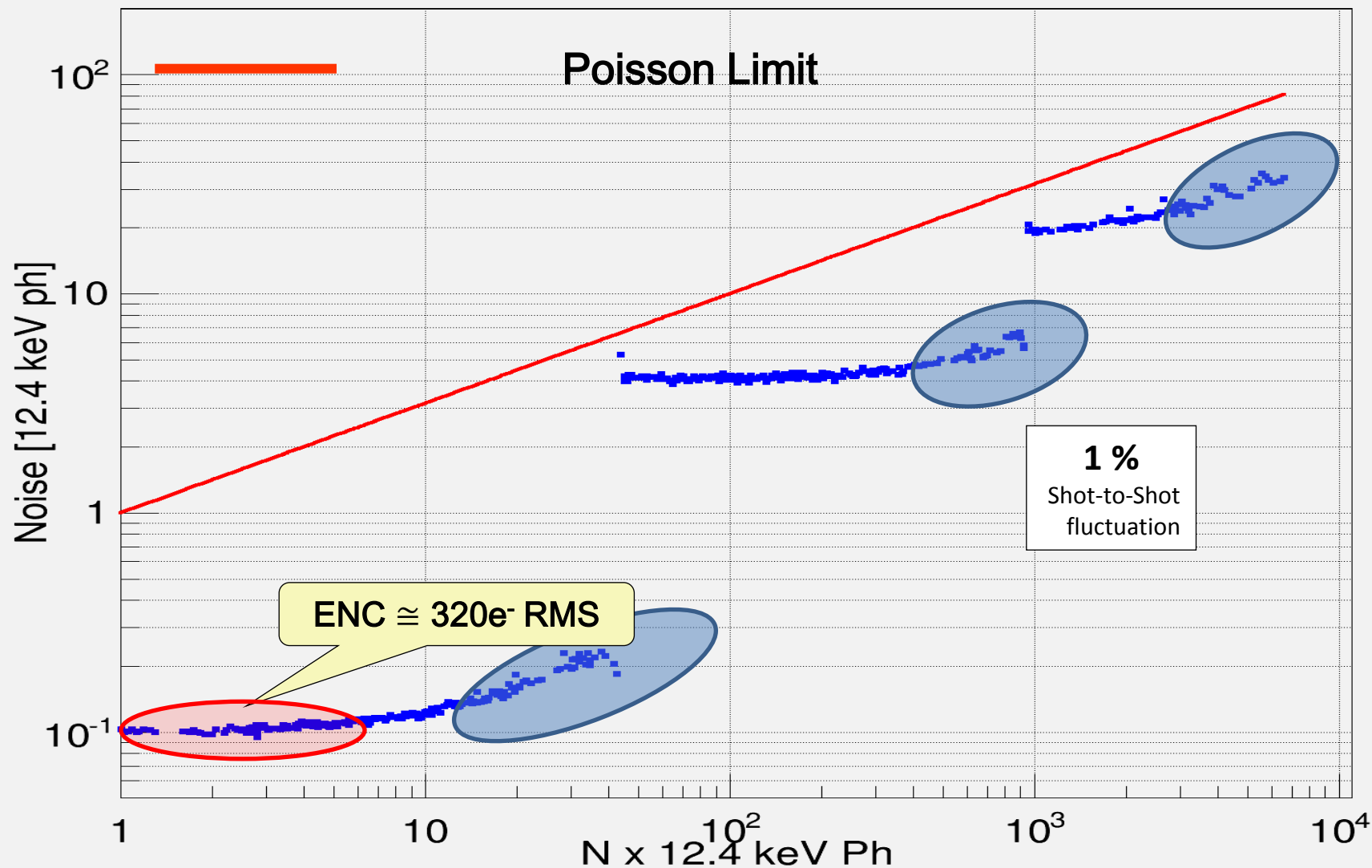


## Dynamic Range Scan: IR Pulsed Laser

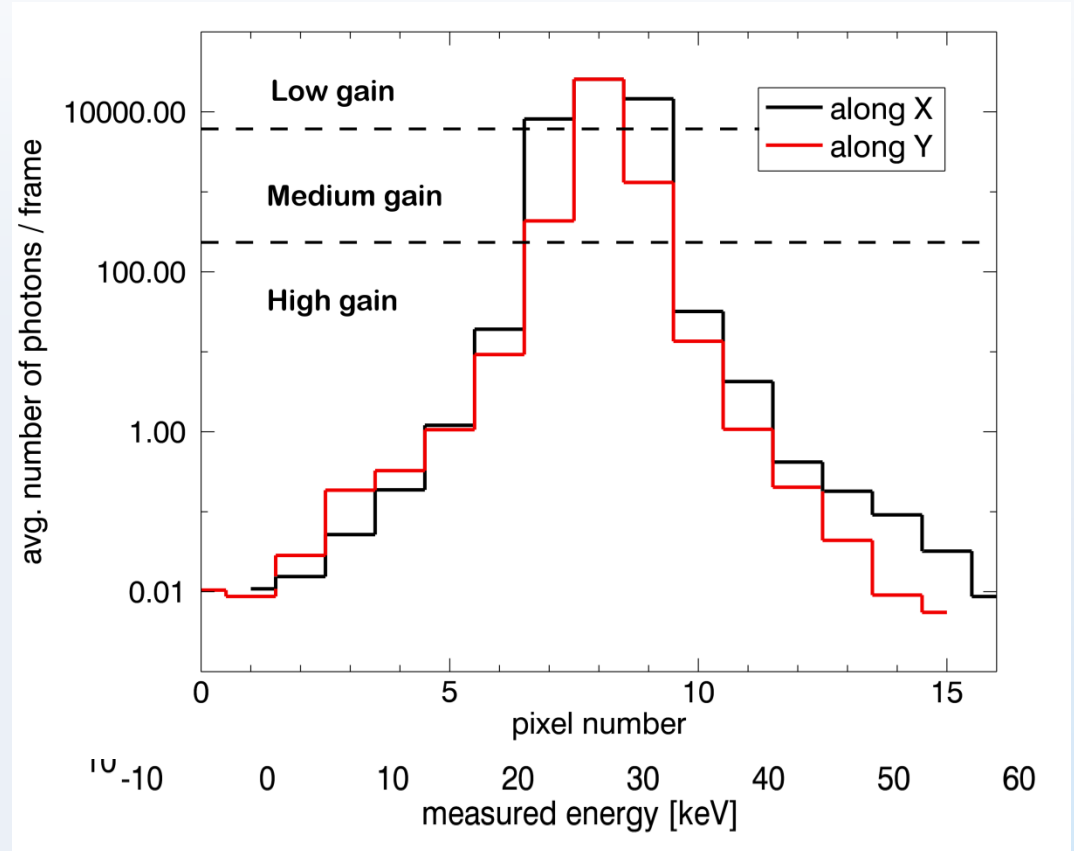
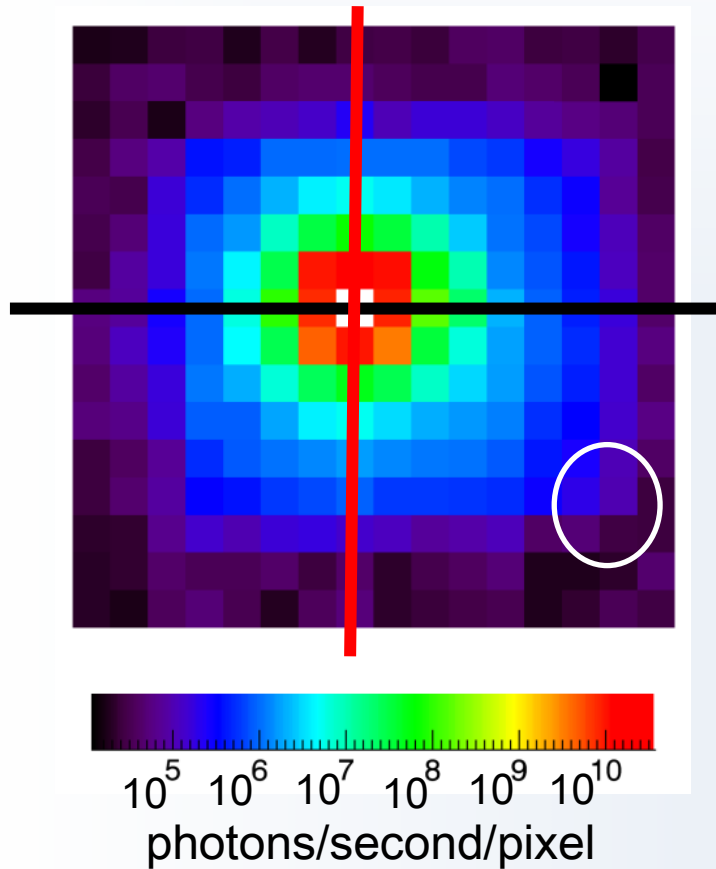


## IR Laser: Noise over Dynamic Range

Noise Over Dynamic Range, IR Laser, Settling time = 145 ns, Chip 1, Vrefcds = 650 mV, No Cooling



# Looking at the direct P10 beam



Gain switching experimentally proven

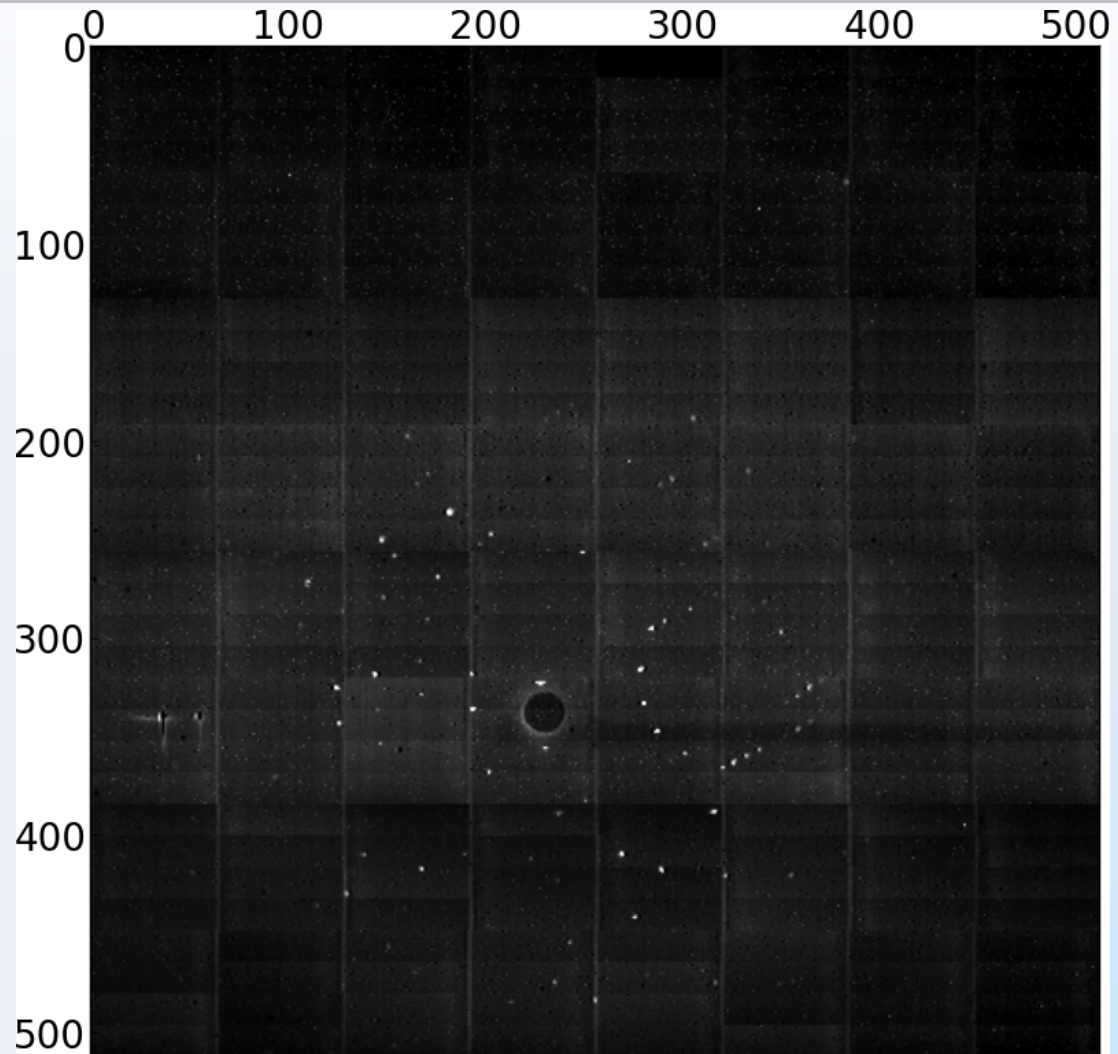
- $10^4$  photons / pulse
- Single photon sensitivity
- 4.5 MHz frame rate

# Protein crystallography at P10



## The experiment:

- Full quadrant
- Lysozyme crystals.
- Bursts of 352 images for each orientation
- $E=9.4$  keV
- No gain or flat field correction applied yet



P10 – PETRA III



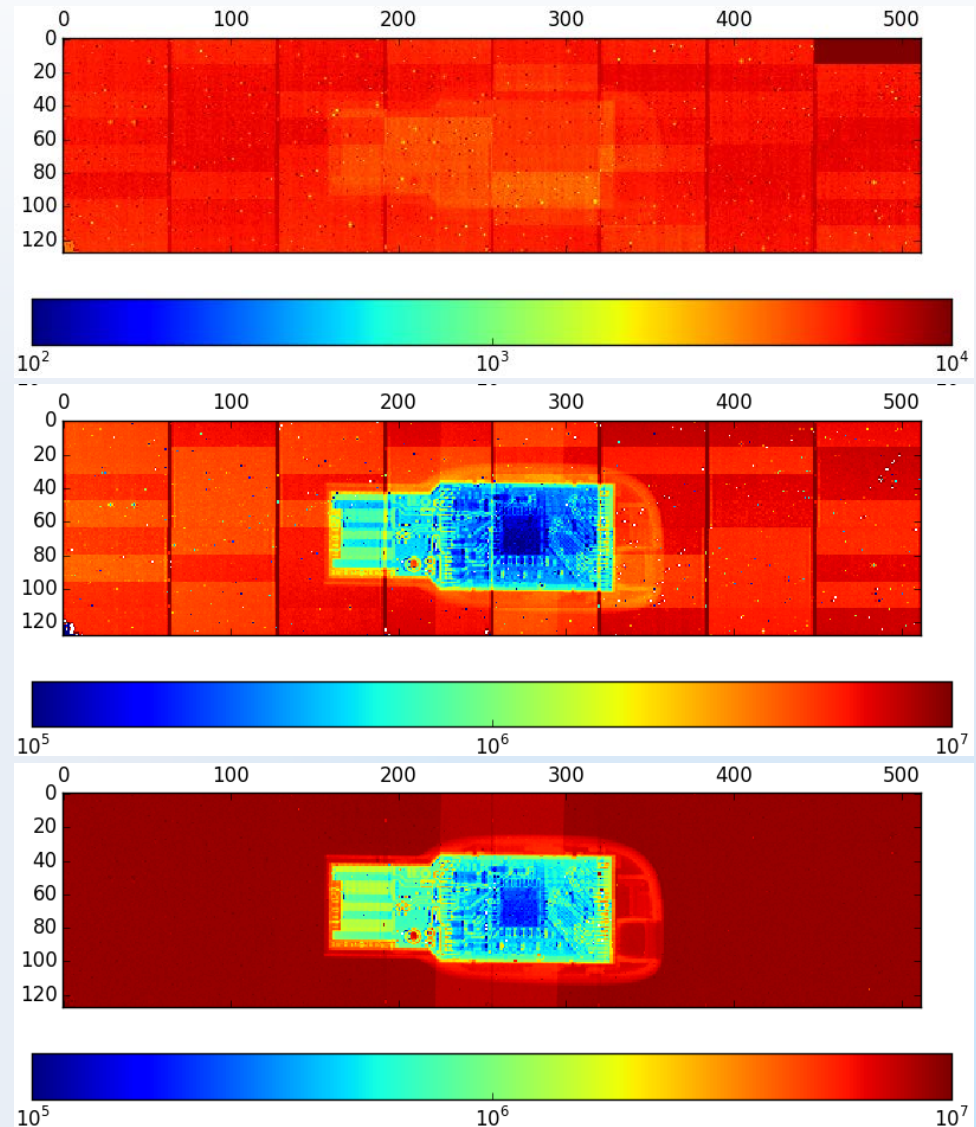
# Calibration is key



- Mean of 30000 frames
- 50 $\mu$ s integration time per frame

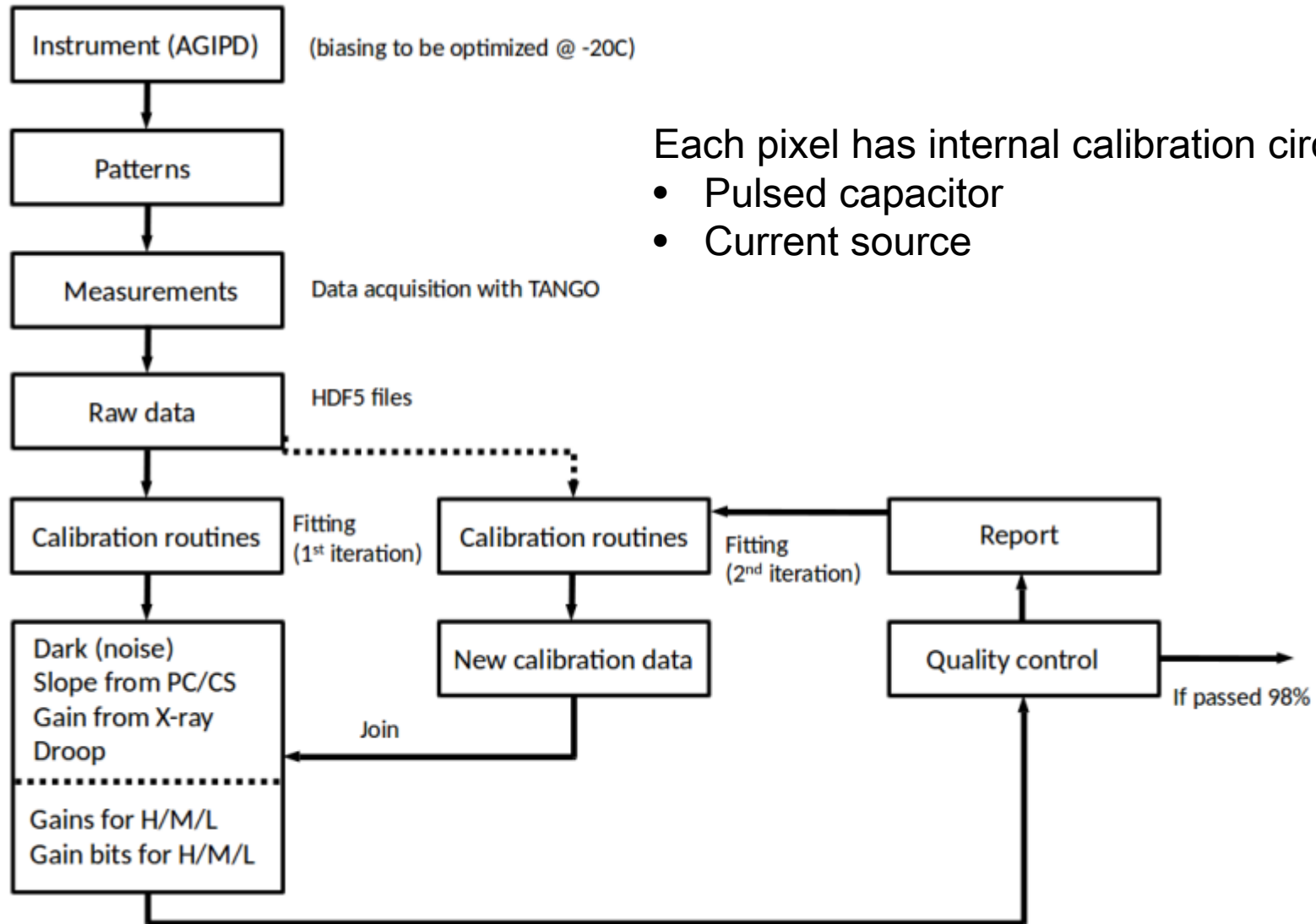
- After dark field correction

- After flat field correction





# Calibration Framework



# AGIPD 1Mpix Systems

(SPB and MID Beamlines at European XFEL)



Independently  
movable  
quadrants

Modules of  
2x8 chips

Arbitrary hole in  
size & shape

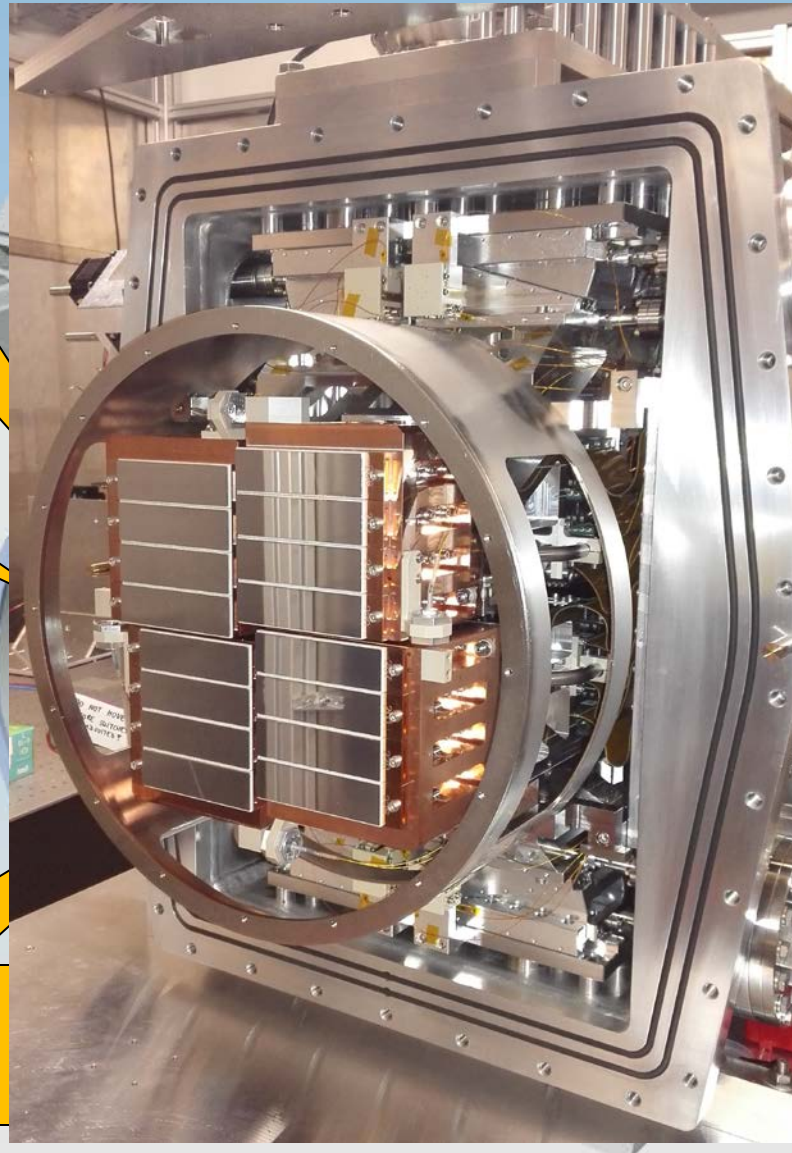
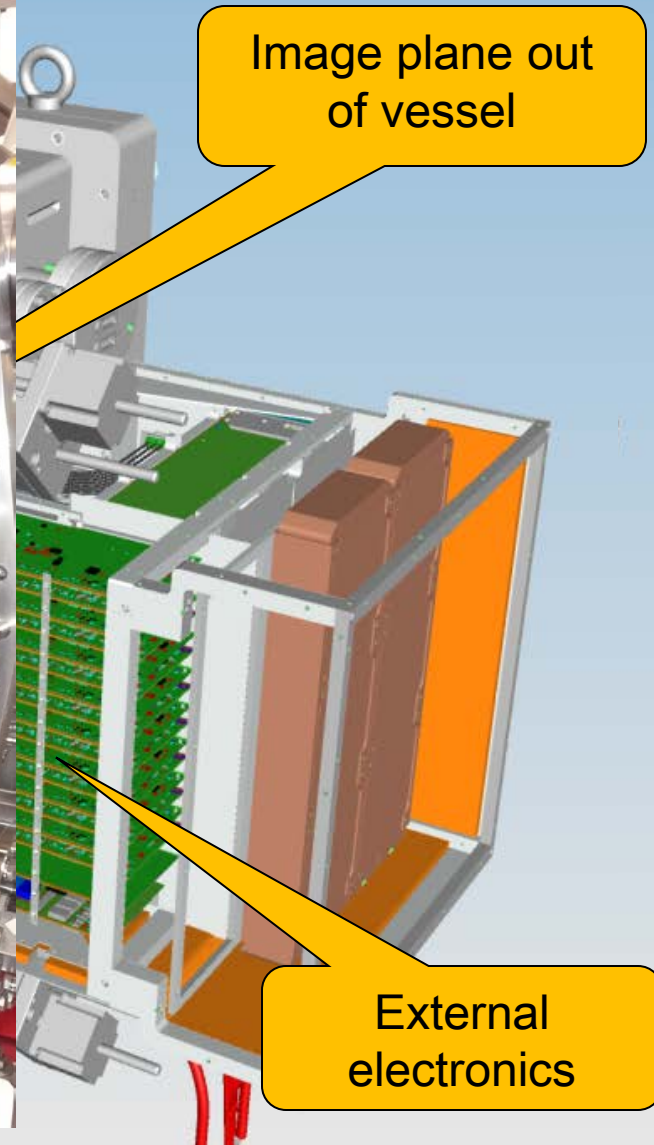


Image plane out  
of vessel



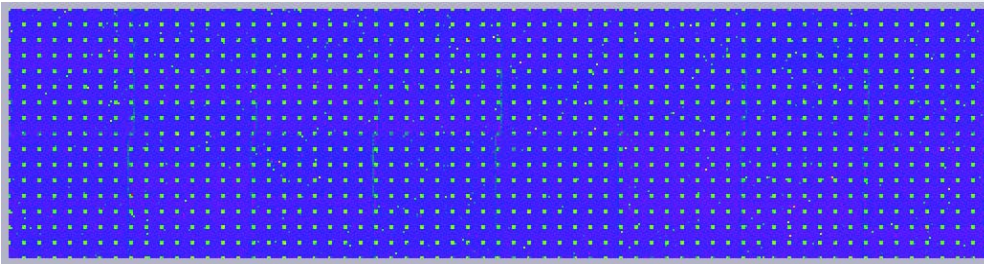
External  
electronics

# First System Testing



Using internal calibration circuitry:

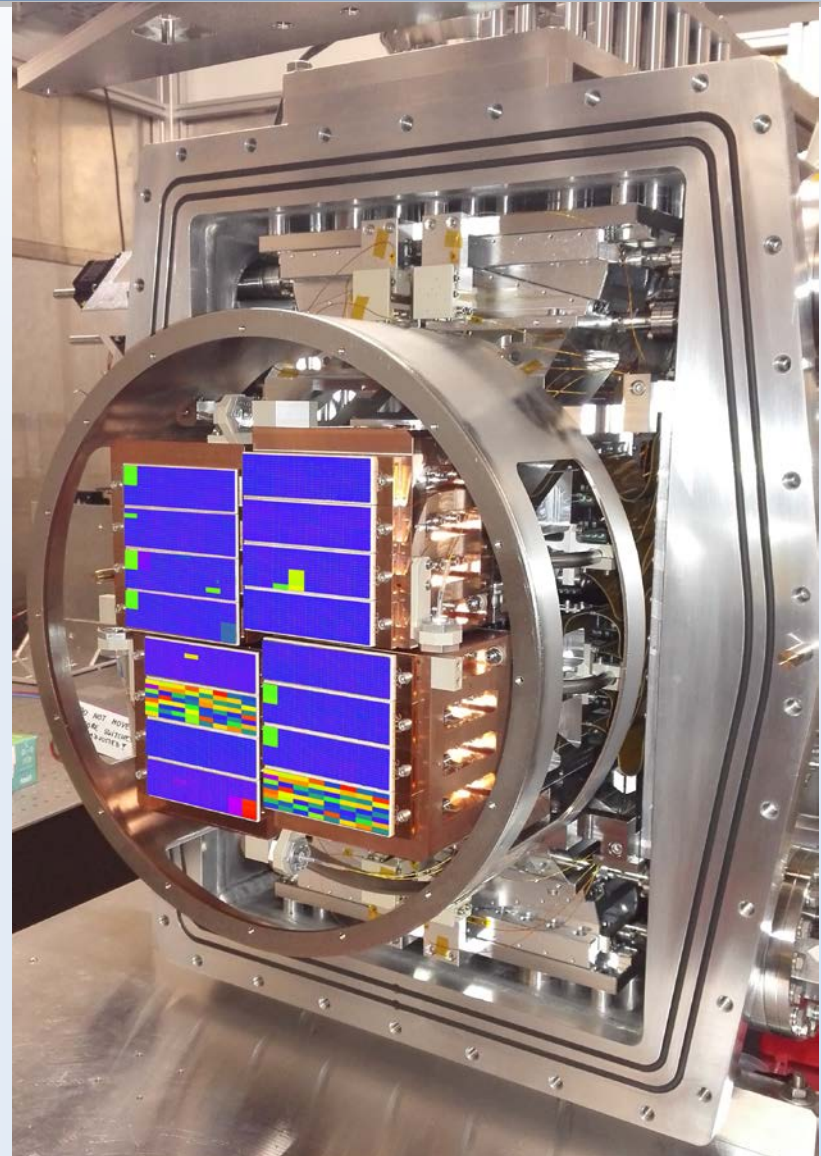
- record a test pattern
- read out detector



- Two modules have a short
  - 5 modules have top left ASIC disabled
- ==> System has been opened this week

Please note:

**modules were build with  
untested AGIPD 1.0 chips**



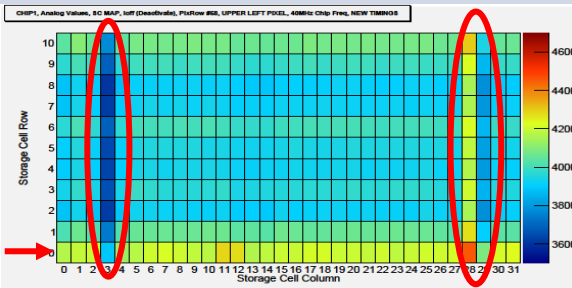


# Second version of chip: AGIPD1.1

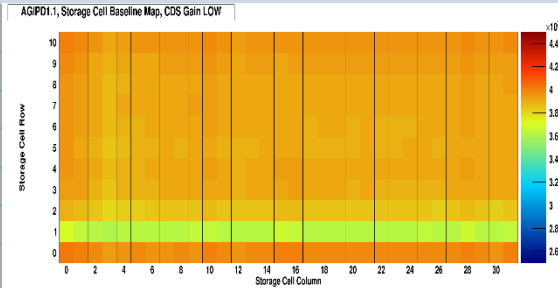


## AGIPD 1.0

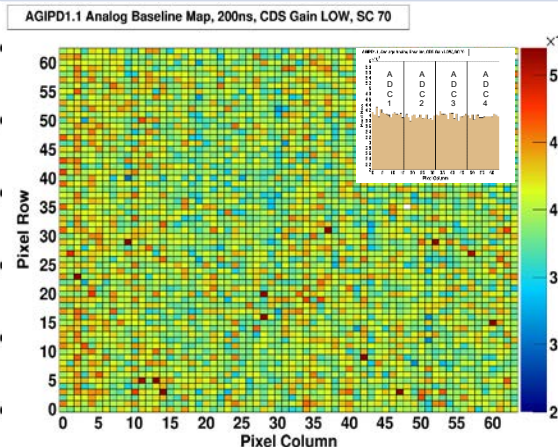
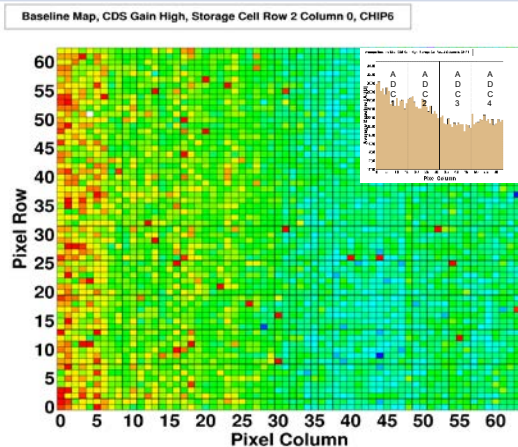
### Memory Map (Baseline)



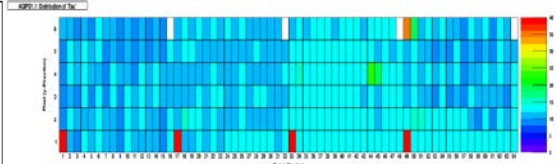
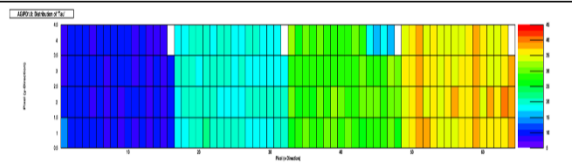
## AGIPD 1.1



### Pixel Map (Baseline)



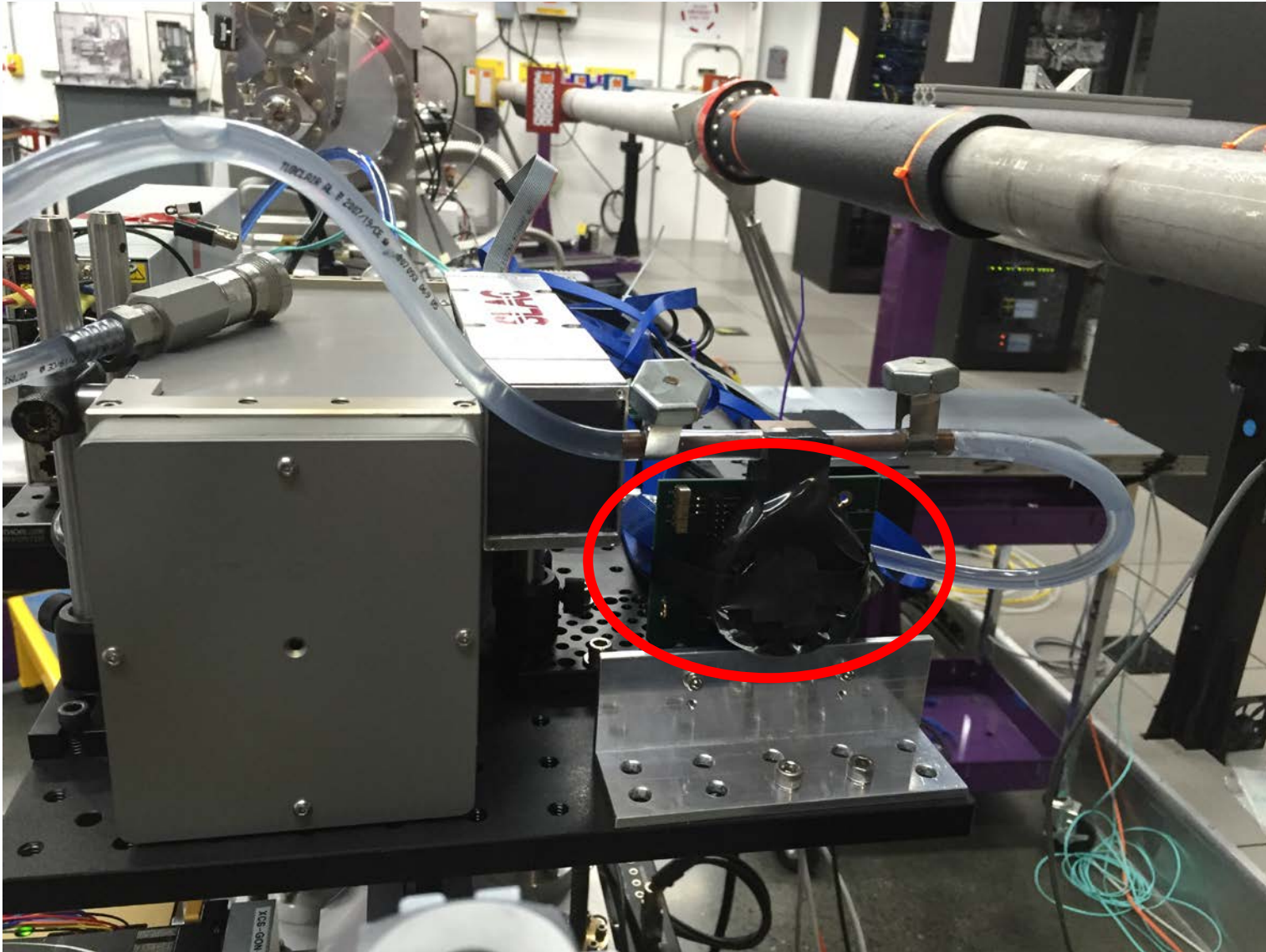
### Output Speed (Rise Time)



Back from foundry end of February 2016

- New calibration circuits
  - Better range & granularity
- Different encoding & readout of gain signals
  - Easier discrimination
  - No level adjustment for readout
- Improved routing inside the pixel
  - Lower crosstalk
  - Homogeneous pedestal map
  - No interference with calibration circuit
- Improved power distribution
  - Lower gain dispersion
  - Better pedestal homogeneity
  - Shorter (CDS) settling times
- Reworked readout lines
  - Lower capacitance & resistance
  - Higher readout speed
  - Lower speed dispersion between analogue ports
- Individual buffering of off-chip driver reference voltage
  - Eliminates 'Ghosting' crosstalk
- On-chip filter caps
  - Improved stability
- New Power-up reset
- Stronger buffers for MUX clock and token
- .....

# AGIPD 1.1 being put to the test

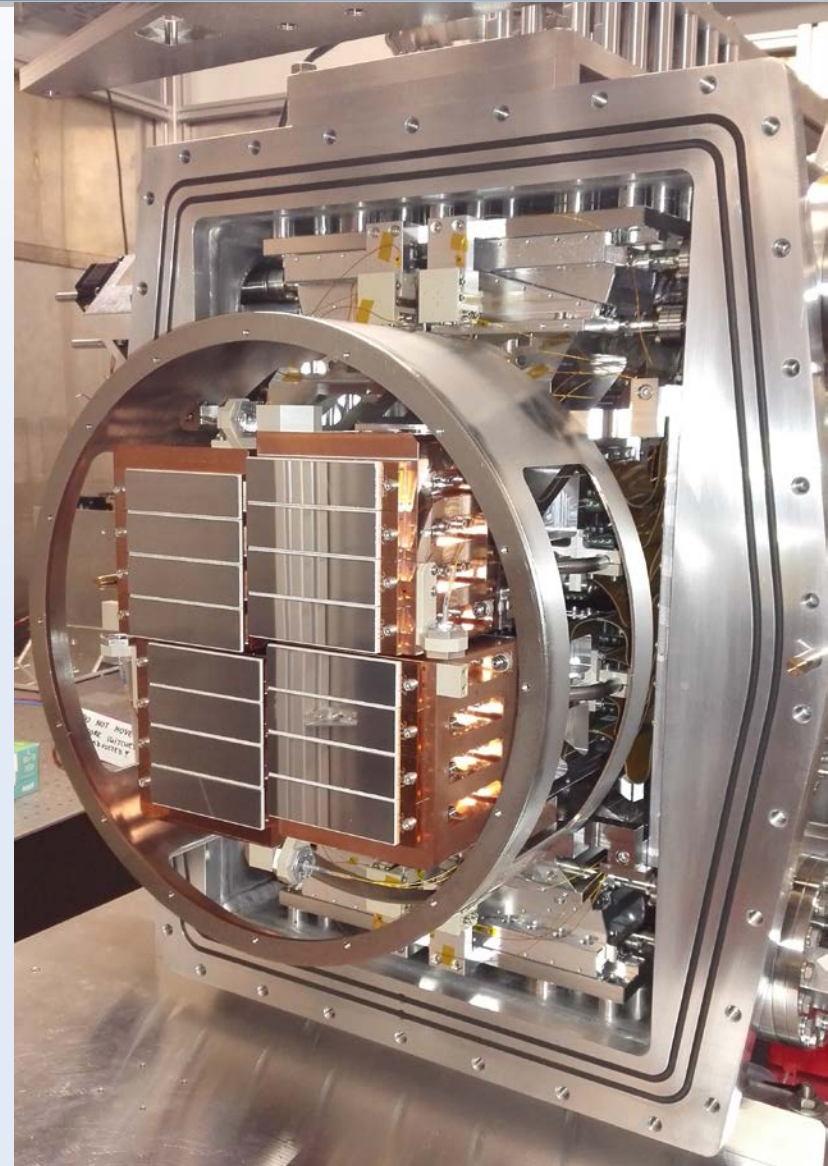




# AGIPD 1.1 being put to the test



- Handover of 1<sup>st</sup> 1M-system (SPB) October 2016 (with AGIPD 1.0)
- Replacement of AGIPD 1.0 with AGIPD 1.1 for SPB early 2017 (before first beam)
- Handover second 1M-system (MID) early 2017 (with AGIPD 1.1)
- Development of 4M system for SFX (new layout of electronics) has started (see H. Chapman's talk)

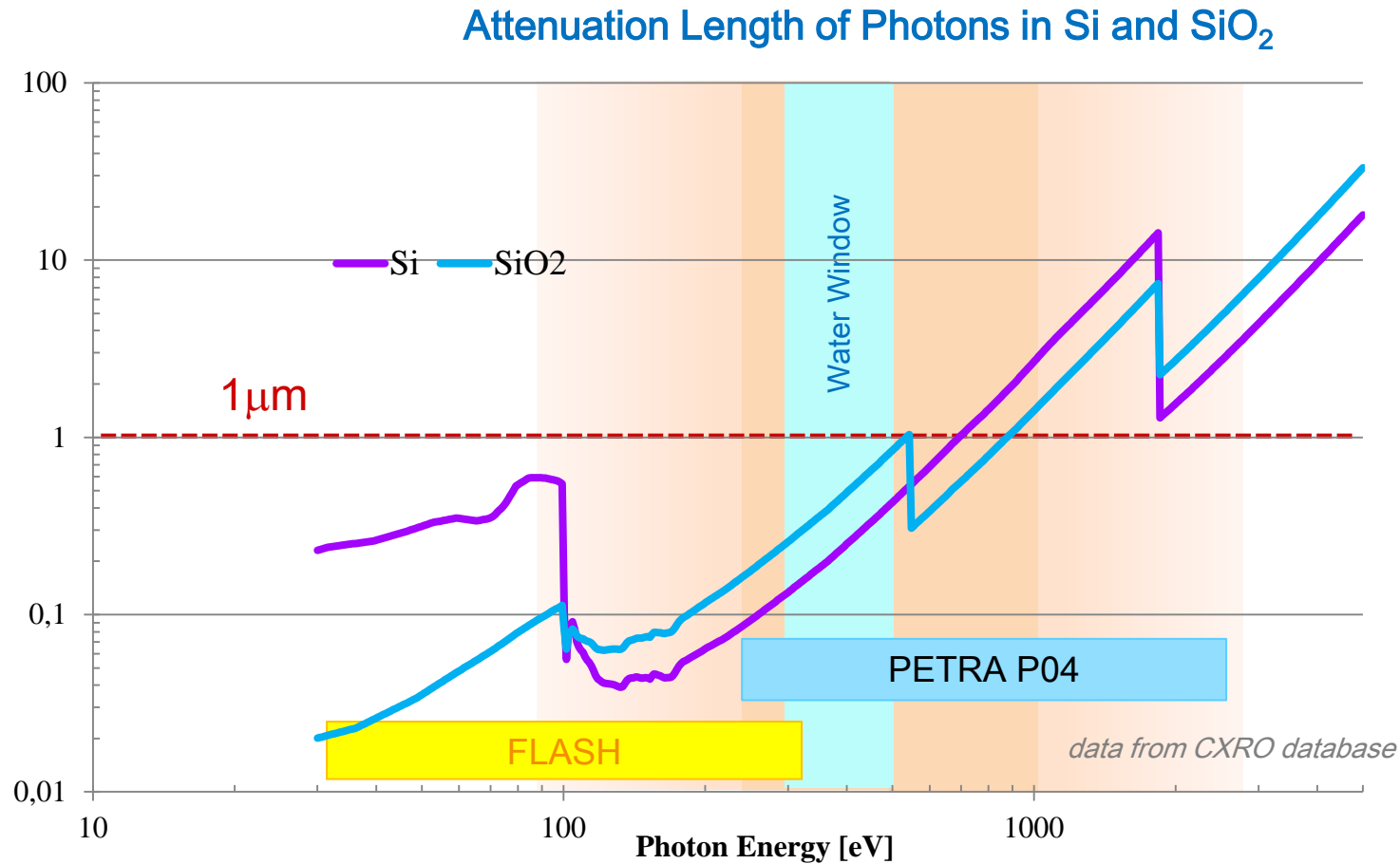




(Pixelated Energy Resolving CMOS Imager, Versatile And Large)



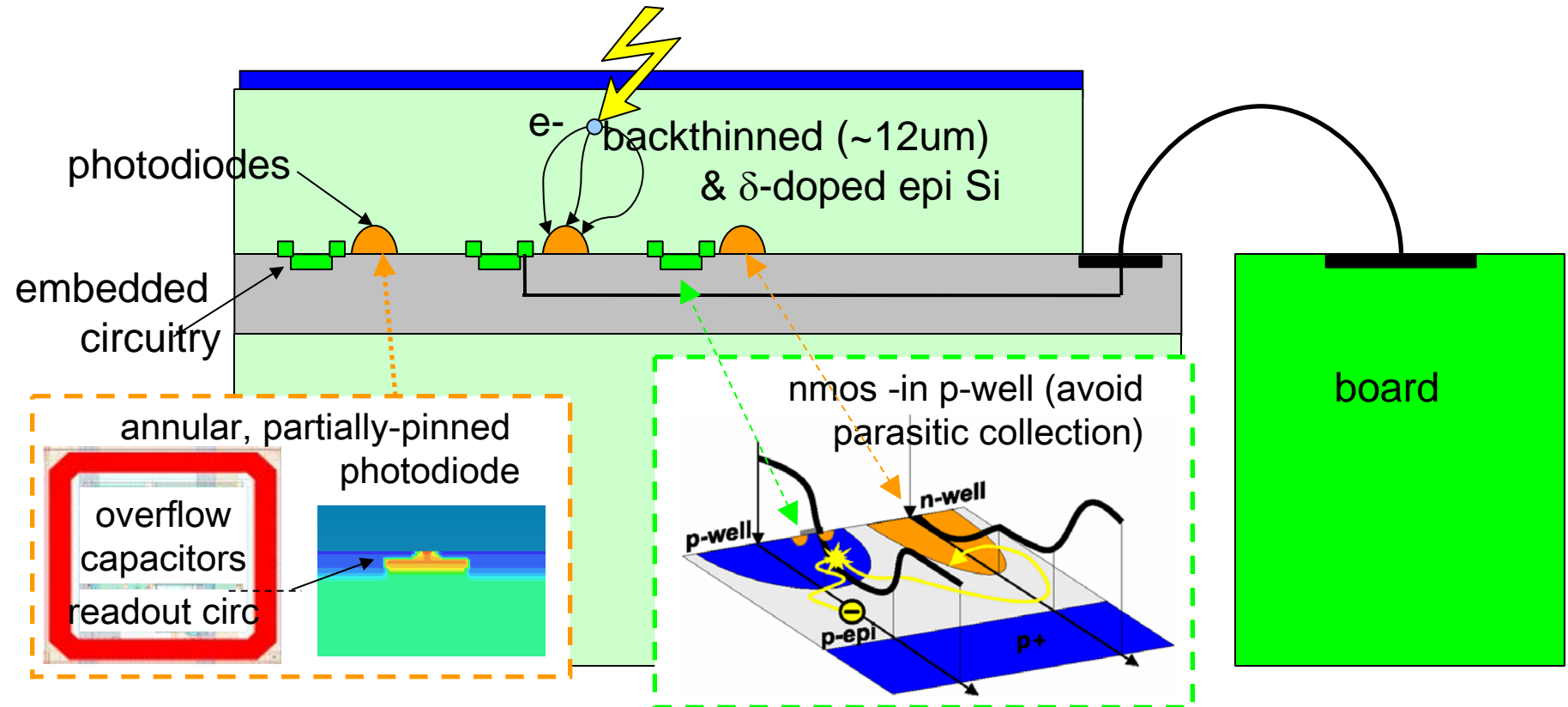
# Soft X-ray Challenges – reaching the sensor



*At (very) soft X-ray energies, QE is limited by passive window thickness!*

*e.g. 50 nm of SiO<sub>2</sub>: loss of 25% of 250 eV photons*

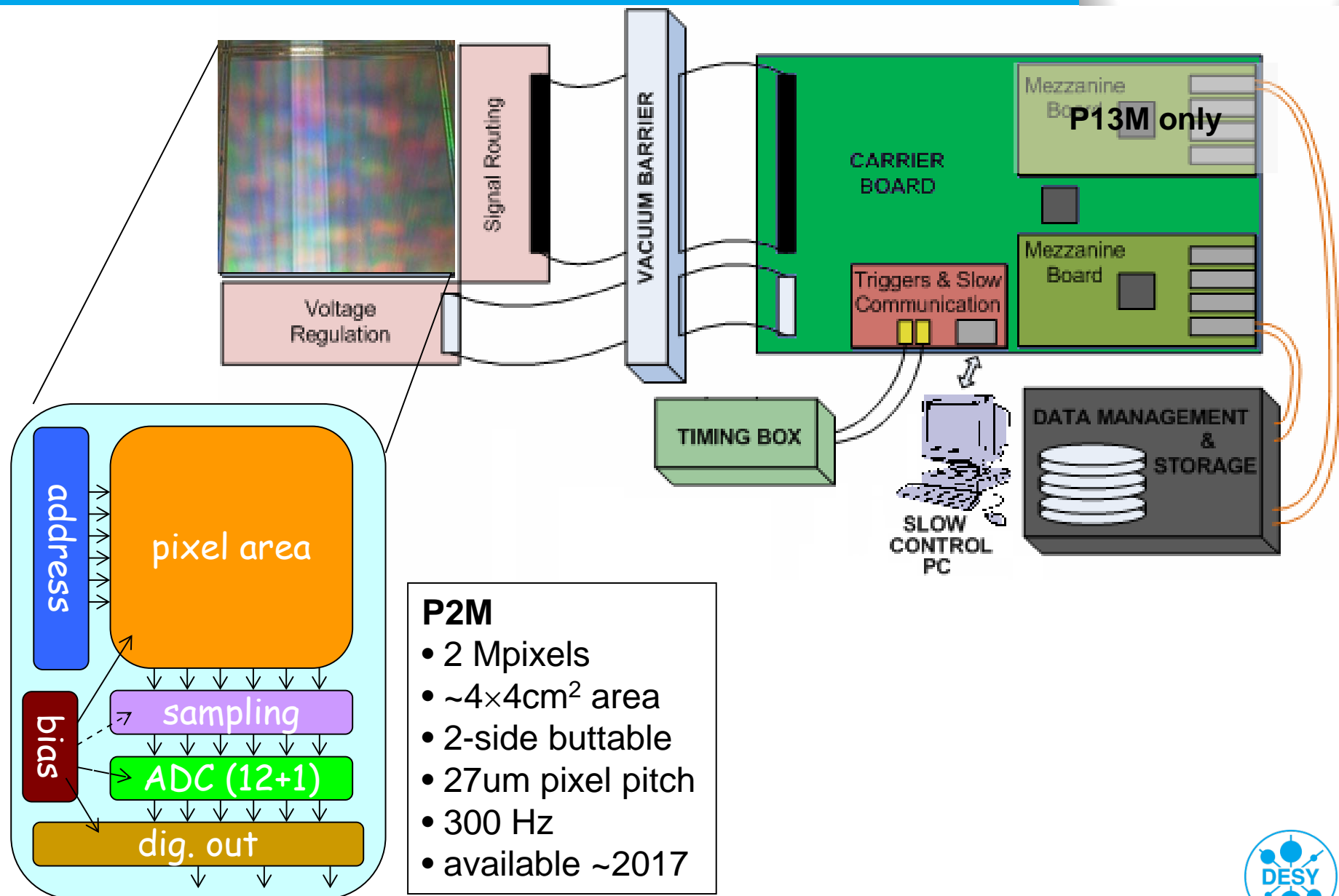
# Monolithic Active Pixel Sensor



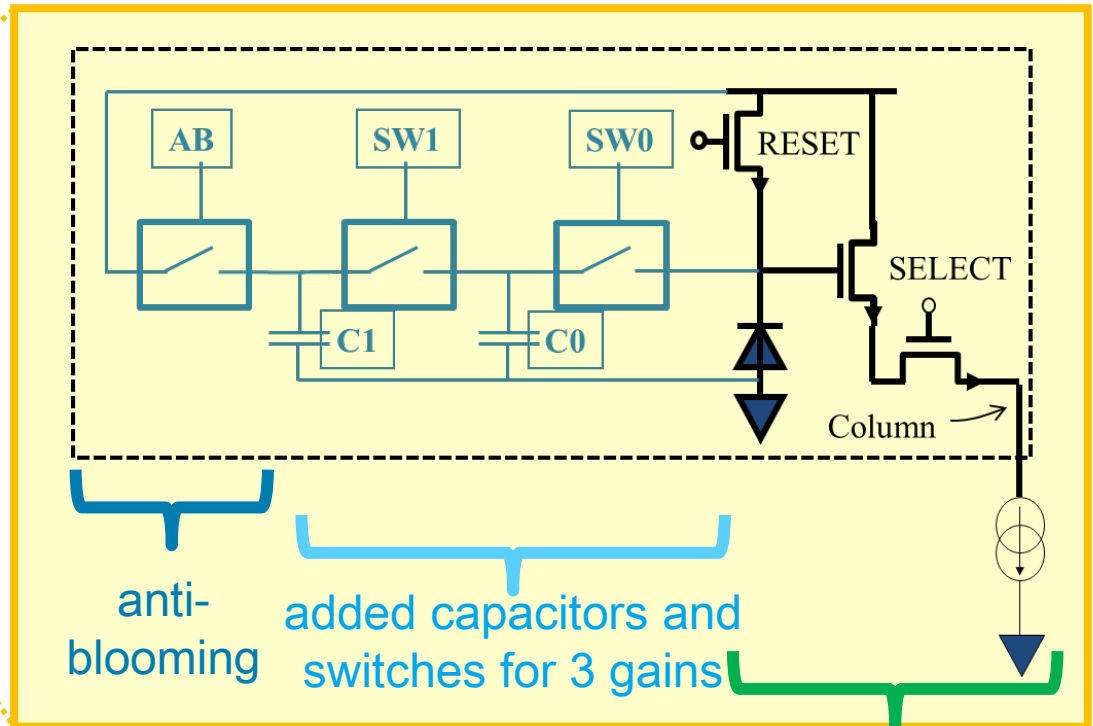
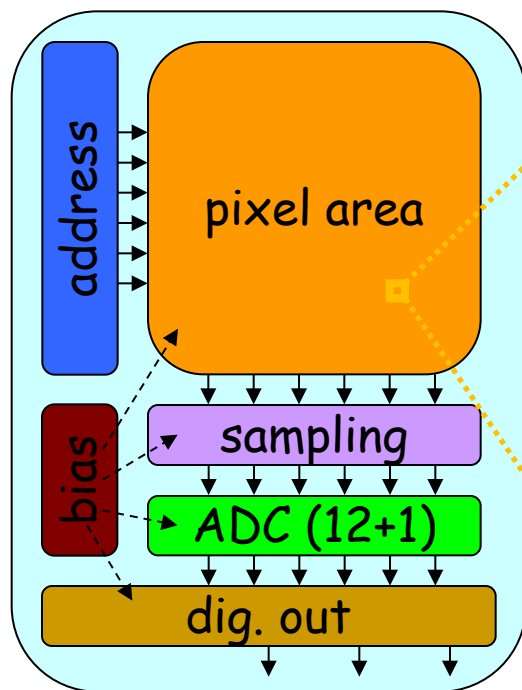
Monolithic: Collecting diodes & readout circuitry share the same substrate  
TowerJazz 0.18 $\mu\text{m}$  CMOS techn, over high-resistance thick epi  
Coupled to handling wafer, back-thinned, back-illuminated: 100% fill factor  
Back surface delta-doped, post-processed: almost no entrance window



# The full PERCIVAL system



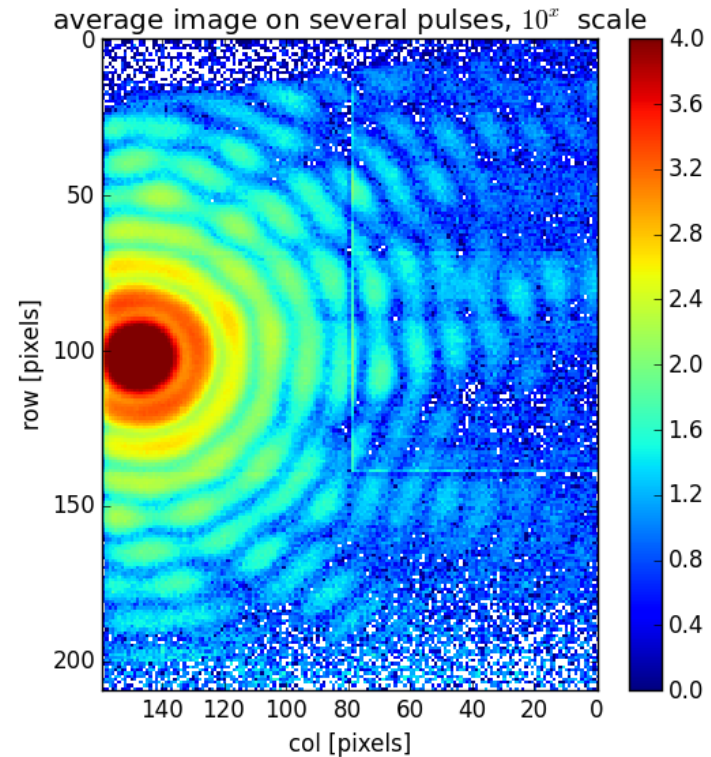
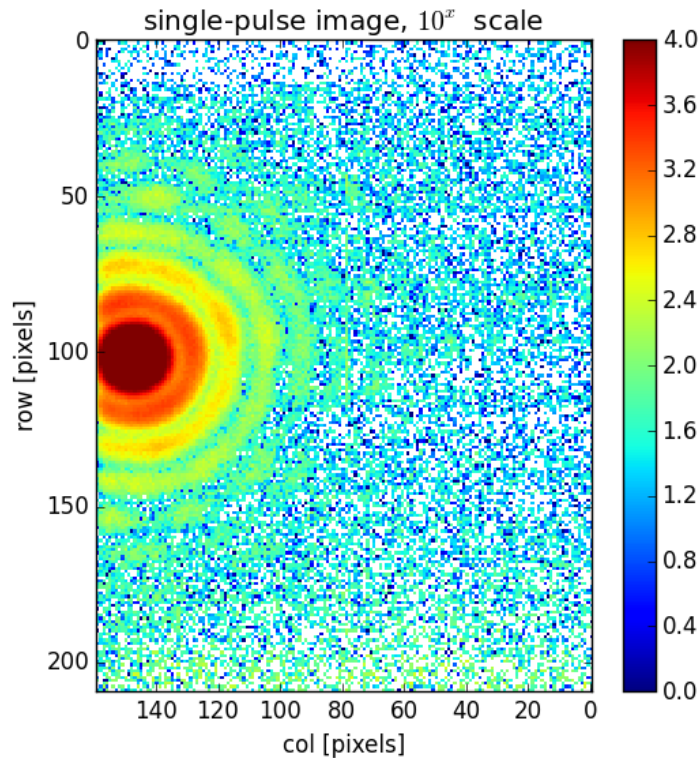
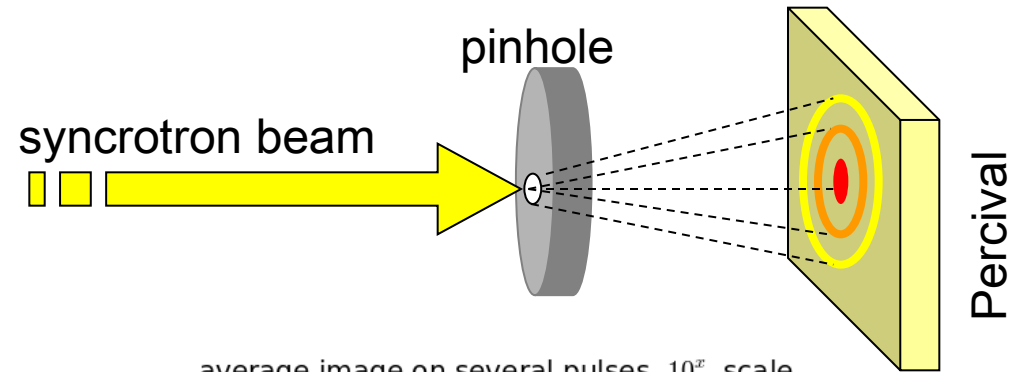
# The Percival Sensor



"standard"  
3T pixel

# single pulse imaging @ FEL: test results

tests at BL2 (Flash)  
single-pulse imaging (10Hz)  
92eV



# Summary – the short version



single  
photon  
resolution!

< 100eV ...

**250eV-1keV**



... few keV

low  
noise!



When?

1<sup>st</sup> half 2017



high  
dynamic  
range!

many  
frames/s !



high QE!  
**TBC**

No blind  
areas !



many pixels!  
small pixels!

2- side buttable!  
(even more pixels)



- First AGIPD 1M (SPB) ready for delivery in October 2016
- Replacement with new chips (SPB) before first beam (fully calibrated)
- Second AGIPD 1M (MID) being assembled; delivery early 2017
- AGIPD 4M (SFX) under development
- PERCIVAL proven imaging from 92 eV to 2 keV
- PERCIVAL 2M expected back from foundry October, BSI chips spring 2017